



170

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Kuo-Chuan Liu, et al.

Serial No.: 10/807,605

Filed: March 23, 2004

For: Methods of Forming LaNiO₃
Conductive Layers, Ferro-Electric
Devices with LaNiO₃ Layers, and
Precursor Formation Solutions

Art Unit: 1762

Examiner: Unknown

Atty. Dkt.: 02EK-105600

**CERTIFICATE OF
MAILING/TRANSMISSION
(37 C.F.R. § 1.8A)**

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PURSUANT TO 37 C.F.R. §1.56 AND §§1.97-1.98**

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Sir:

The citations listed on the enclosed PTO-1449 Form are submitted under 37 C.F.R.
§§1.97 and 1.98, and in compliance with the duty of disclosure as defined in 37 C.F.R. §1.56.

The Examiner is requested to make these citations officially of record in the application.
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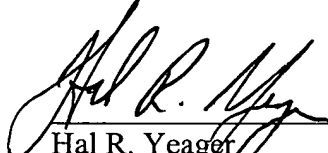
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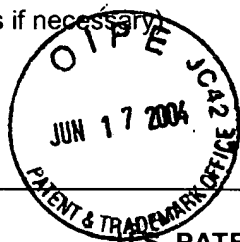
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Respectfully submitted,



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FORM PTO-1449 (Modified) LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT(S)' INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	ATTY. DOCKET NO. 02EK-105600	SERIAL NO. 10/807,605
	APPLICANT: Kuo-Chuan Liu, et al.	
	FILING DATE: March 23, 2004	GROUP ART UNIT: 1762



REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAM'R INITIAL		DOCUMENT NUMBER	DATE	NAME	Class	Subclass	Filing Date If Appropriate
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FOREIGN PATENT DOCUMENTS

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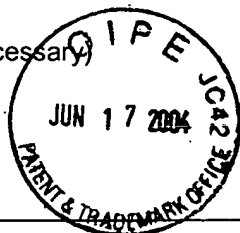
OTHER ART (Include Author, Title, Date, Pertinent Pages, Etc.)

C1	K.M. Satyalakshmi, et al., "Epitaxial metallic LaNiO ₃ thin films grown by pulsed laser deposition," <i>Appl. Phys. Lett.</i> 62:11 (1993) 1233-1235.
C2	C.C. Yang, et al., "Preparation of (100)-oriented metallic LaNiO ₃ thin films on Si substrates by radio frequency magnetron sputtering for the growth of textured Pb(Zr _{0.53} Ti _{0.47})O ₃ ," <i>Appl. Phys. Lett.</i> 66:20 (1995) 2643-2645.
C3	Y.L. Tu, et al., "Synthesis and Electrical Characterization of Thin Films of PT and PZT Made from a Diol-Based Sol-Gel Route," <i>J. Am. Ceram. Soc.</i> 79:2 (1996) 441-448.
C4	A. Li, et al., "Preparation of perovskite conductive LaNiO ₃ films by metalorganic decomposition," <i>Appl. Phys. Lett.</i> 68:10 (1996) 1347-1349.
C5	M.S. Chen, et al., "Effect of textured LaNiO ₃ electrode on the fatigue improvement of Pb(Zr _{0.53} Ti _{0.47})O ₃ thin films," <i>Appl. Phys. Lett.</i> 68:10 (1996) 1430-1432.
C6	T.F. Tseng, et al., "Effect of LaNiO ₃ /Pt double layers on the characteristics of (Pb _x La _{1-x})(Zr _y Ti _{1-y})O ₃ thin films," <i>Appl. Phys. Lett.</i> 68:18 (1996) 2505-2510.
C7	A. Li, et al., "Preparation of epitaxial metallic LaNiO ₃ films on SrTiO ₃ by metalorganic decomposition for the oriented growth of PbTiO ₃ ," <i>Appl. Phys. Lett.</i> 69:2 (1996) 161-163.

EXAMINER	DATE CONSIDERED
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	A1						
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							yes	no
	B1							

OTHER ART (Include Author, Title, Date, Pertinent Pages, Etc.)

C8	T. Yu, et al., "Epitaxial Pb(Zr _{0.53} Ti _{0.47})O ₃ /LaNiO ₃ heterostructures on single crystal substrates," <i>Appl. Phys. Lett.</i> 69:14 (1996) 2092-2094.
C9	Y.L. Tu, et al., "Processing and characterization of Pb(Zr, Ti)O ₃ films, up to 10 μm thick, produced from a diol sol-gel route," <i>J. Mater. Res.</i> 11:10 (1996) 2556-2564.
C10	A. Li, et al., "Fabrication and electrical properties of sol-gel derived BaTiO ₃ films with metallic LaNiO ₃ electrode," <i>Appl. Phys. Lett.</i> 70:12 (1997) 1616-1618.
C11	C. R. Cho, et al., "Solution deposition and heteroepitaxial crystallization of LaNiO ₃ electrodes for integrated ferroelectric devices," <i>Appl. Phys. Lett.</i> 71:20 (1997) 3013-3015.
C12	R. Kurchania, et al., "Synthesis of (Pb,Lu) (Zr,Ti)O ₃ films using a diol based sol-gel route," <i>J. Mater. Sci.</i> 33 (1998) 659-667.
C13	C.H. Lin, et al., "Domain structure and electrical properties of highly textured PbZr _x Ti _{1-x} O ₃ thin films grown on LaNiO ₃ -electrode-buffered Si by metalorganic chemical vapor deposition," <i>J. Mater. Res.</i> 15:1 (2000) pp. 115-124.
C14	S.S. Kim, et al., "Structures and properties of (001)-oriented Pb(Zr,Ti)O ₃ films on LaNiO ₃ /Si(001) substrates by pulsed laser deposition," <i>J. Mater. Res.</i> 15:12 (2000) 2881-2886.
C15	G.S. Wang, et al., "Properties of highly (100) oriented Ba _{0.9} Sr _{0.1} TiO ₃ /LaNiO ₃ heterostructures prepared by chemical solution routes," <i>Appl. Phys. Lett.</i> 78:26 (2001) 4172-4174.

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